

Receipt date: 07/28/2009

SHEET 1 OF 2

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

 ATTY. DOCKET NO.  
**061282-0234**

 SERIAL NO.  
**10/574,863**

 APPLICANT  
**Yuichiro SASAKI, et al.**

(Substitute for form 1449/PTO)

 FILING DATE  
**April 06, 2006**

 GROUP  
**2823**

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US 5,915,196	06-22-1999	MINEJI	
		US 6,153,524	11-28-2000	HENLEY et al.	
		US 6,159,810	12-12-2000	YANG	
		US 2002/0112951 A1	08-22-2002	FAN	
		US 5,407,845	04-18-1995	NASU et al.	Corresponds to JP 2530990 B2
		US 5,956,581	09-21-1999	YAMAZAKI et al.	
		US 5,892,235	04-06-1999	YAMAZAKI et al.	
		US 5,915,196	06-22-1999	MINEJI	
		US 6,153,524	11-28-2000	HENLEY et al.	
		US 6,159,810	12-12-2000	YANG	
		US 2002/0112951 A1	08-22-2002	FAN	
		US 6,013,332	01-11-2000	Goto et al.	
		US 6,583,018 B1	06-24-2003	Matsunaga et al.	
		US 6,013,332	01-11-2000	GOTO et al.	Corresponds to JP 10-163123

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
		<del>WO 03/014979 A</del>	<del>02-20-2003</del>	<del>APPLIED MATERIALS, INC.</del>		<del>X</del>
		<del>JP 2530990 B2</del>	<del>09-04-1996</del>	<del>FUJITSU LTD</del>	<del>Corresponds to US 5,407,845</del>	<del>X</del>
		<del>JP 03-215638</del>	<del>09-26-1991</del>	<del>SEIKO INSTR INC</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 6-89904</del>	<del>03/29/1994</del>	<del>SEMICONDUCTOR ENERGY LAB</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 10-163123</del>	<del>06/19/1998</del>	<del>FUJITSU LTD; KAGAKU GIJUTSU SHINKO JIGYODAN</del>	<del>Corresponds to US 6,013,332</del>	<del>JAPAN (w/English Abstract)</del>

## OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005
		International Search Report issued in International Patent Application No. PCT/JP2004/015308 mailed January 18, 2005
		Japanese Notification of Reasons for Refusal, w/ English translation thereof, issued in Japanese Patent Application No. JP 2005-502685 dated May 19, 2009
		European Search Report issued in European Patent Application No. EP 04710478 dated May 12, 2009

EXAMINER

DATE CONSIDERED

George Fournon

11/25/2009

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /GF/

\* no copies submitted for lined through references

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Substitute for form 1449/PTO)

 ATTY. DOCKET NO.  
**061282-0234**

 SERIAL NO.  
**10/574,863**

 APPLICANT  
**Yuichiro SASAKI, et al.**

 FILING DATE  
**April 06, 2006**

 GROUP  
**2823**

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US 2002/0006689 A1	01-17-2002	MIYASAKA, MITSUTOSHI	

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code-Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
		<del>JP 7-142421</del>	<del>06-02-1995</del>	<del>NIPPON ELECTRIC CO</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 2003-86528</del>	<del>03-20-2003</del>	<del>DENSO CORP</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 2003-7638</del>	<del>01-10-2003</del>	<del>SONY CORP</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 6-279475</del>	<del>10-22-1996</del>	<del>MURATA MANUFACTURING CO</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 2000-12481</del>	<del>01-14-2000</del>	<del>APPLIED MATERIALS INC</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 2004-14878</del>	<del>01-15-2004</del>	<del>SHARP KK</del>		<del>JAPAN (w/English Abstract)</del>
		<del>JP 2004-158627</del>	<del>06-03-2004</del>	<del>RENESAS TECH CORP; ION ENGINEERING RESINST CORP; TSUBOUCHI NATSUGO</del>		<del>JAPAN (w/English Abstract)</del>

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		<del>TSUTSUMI, K., et al., "Contribution and Control of Neutral Gas Absorption Effects in the Plasma Doping of Boron into Si", 2004, pages 46-49, IEEE.</del>
		<del>BAEK, S., et al., "Characteristics of Low-Temperature Preannealing Effects on Laser-Annealed P/N and N/P Ultra-Shallow Junctions", 2004, pages 54-57, IEEE.</del>
		<del>SEMICONDUCTOR APPLICATIONS, MICROCAVITY ENGINEERING, TRENCH DOPING, pages 662-667</del>
		<del>R. SIEGELE, et al., "Helium Bubbles in Silicon: Structure and Optical Properties," Appl. Phys. Lett. 66 (11), 13 March 1995, pp. 1319-1321</del>
		<del>V.F. REUTOV &amp; A.S. SOKHATSKII, "Helium Ion Bombardment Induced Amorphization of Silicon Crystals," Technical Physics Letters, Vol. 38, No. 7, 2002, pp. 615-617</del>
EXAMINER		DATE CONSIDERED
/George Fourson/		11/25/2009

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

\* no copies submitted for lined through references

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /GF/